



PTO-1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT	ATTY. DOCKET NO. 211.001-D4-US	SERIAL NUMBER 10/727,742
	APPLICANT(S) Fazan et al.	
	FILING DATE December 4, 2003	GROUP ART UNIT

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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
<i>JH</i>	4,032,947	6/1977	Kesel et al.	257	214	
<i>JH</i>	3,997,799	12/1976	Baker	365	183	
<i>JH</i>	5,448,513	9/1995	Hu et al.	365	150	
<i>JH</i>	4,298,962	11/1981	Hamano et al.	365	182	
<i>JH</i>	3,439,214	4/1969	Kabell	315	11	
<i>JH</i>	6,081,443	6/2000	Morishita	365	149	
<i>JH</i>	6,111,778	8/2000	MacDonald et al.	365	149	

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<i>JH</i>	FR 2 197 494	3/1974	French			
<i>JH</i>	EP 1 180 799	2/2002	European			
<i>JH</i>	EP 0 030 856	6/1981	European			
<i>JH</i>	GB 1 414 228	11/1975	Great Britain			
<i>JH</i>	EP 0 694 977	1/1996	European			
<i>JH</i>	JP 02 294076	2/1991	Japanese			
<i>JH</i>	EP 1 237 193	9/2002	European			
<i>JH</i>	EP 0 878 804	11/1998	European			

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<i>JH</i>	"The Multistable Charge-Controlled Memory Effect in SOI MOS Transistors at Low Temperatures", Tack et al., IEEE Transactions on Electron Devices, Vol. 37, No. 5, May 1990, pp.1373-1382

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<i>JE</i>	5,780,906	7/1998	Wu et al.	257	368	
<i>JE</i>	5,144,390	9/1992	Matloubian	257	347	
<i>JE</i>	5,696,718	12/1997	Hartmann	365	185.27	

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<i>JE</i>	EP 0 801 427	10/1997	European			
<i>JE</i>	EP 0 513 923	11/1992	European			

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<i>JH</i>	5,982,003	11/1999	Hu et al.	257	347	
<i>JH</i>	6,121,077	9/2000	Hu et al.	257	347	
<i>JH</i>	6,300,649	10/2001	Hu et al.	257	69	
<i>JH</i>	6,518,105	2/2003	Yang et al.	438	151	
<i>JH</i>	2002 0070411	6/2002	Vermandel et al.			

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<i>JH</i>	EP 0 362 961 B1	2/1994	European			
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<i>JH</i>	"Mechanisms of Charge Modulation in the Floating Body of Triple-Well nMOSFET Capacitor-less DRAMs", Villaret et al., Proceedings of the INFOS 2003, Insulating Films on Semiconductors, 13th Bi-annual Conference, June 18-20, 2003, Barcelona (Spain), (4 pages)

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JH	EP 1 233 454	8/2002	European			
JH	JP 247735	8/2000	Japanese			
JH	JP 274221	9/2000	Japanese			
JH	JP 389106	12/2000	Japanese			
JH	JP 180633	6/2001	Japanese			

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JH	"FBC (Floating Body Cell) for Embedded DRAM on SOI, Inoh et al., 2003 Symposium on VLSI Circuits Digest of Technical Papers, June 2003 (2 pages)
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JM	4,979,014	12/1990	Hieda et al.			
JM	5,258,635	11/1993	Nitayama et al.			

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JM	"Opposite Side Floating Gate SOI FLASH Memory Cell", Lin et al., IEEE, March 2000, pp.12-15
JM	"Advanced TFT SRAM Cell Technology Using a Phase-Shift Lithography", Yamanaka et al., IEEE Transactions on Electron Devices, Vol. 42, No. 7, July 1995, pp.1305-1313
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JM	"An SOI 4 Transistors Self-Refresh Ultra-Low-Voltage Memory Cell", Thomas et al., IEEE, March 2003, pp.401-404
JM	"Design of a SOI Memory Cell", Stanojevic et al., IEEE Proc. 21 st International Conference on Microelectronics (MIEL '97), Vol. 1, NIS, Yugoslavis, 14-17 September 1997, pp.297-300
JM	"Effects of Floating Body on Double Polysilicon Partially Depleted SOI Nonvolatile Memory Cell", Chan et al., IEEE Electron Device Letters, Vol. 24, No. 2, February 2003, pp.75-77
JM	"MOSFET Design Simplifies DRAM", P. Fazan, EE Times, May 14, 2002 (3 pages)
JM	"One of Application of SOI Memory Cell - Memory Array", Lončar et al., IEEE Proc. 22 nd International Conference on Microelectronics (MIEL 2000), Vol. 2, NIŠ, Serbia, 14-17 May 2000, pp.455-458
JM	"A SOI Current Memory for Analog Signal Processing at High Temperature", Portmann et al., 1999 IEEE International SOI Conference, Oct. 1999, pp.18-19
JM	"Chip Level Reliability on SOI Embedded Memory", Kim et al., Proceedings 1998 IEEE International SOI Conference, Oct. 1998, pp.135-139

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JHE	5,886,385	3/1999	Arisumi et al.			1
JHE	5,929,479	7/1999	Oyama			

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JHE	"Programming and Erase with Floating-Body for High Density Low Voltage Flash EEPROM Fabricated on SOI Wafers", Chi et al., Proceedings 1995 IEEE International SOI Conference, Oct. 1995, pp.129-130
JHE	"Measurement of Transient Effects in SOI DRAM/SRAM Access Transistors", A. Wei, IEEE Electron Device Letters, Vol. 17, No. 5, May 1996, pp.193-195
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JHE	"A Simple 1-Transistor Capacitor-Less Memory Cell for High Performance Embedded DRAMs", Fazan et al., IEEE 2002 Custom Integrated Circuits Conference, June 2002, pp.99-102
JHE	"A Novel Pattern Transfer Process for Bonded SOI Giga-bit DRAMs", Lee et al., Proceedings 1996 IEEE International SOI Conference, Oct. 1996, pp.114-115
JHE	"An Experimental 2-bit/Cell Storage DRAM for Macrocell or Memory-on-Logic Application", Furuyama et al., IEEE Journal of Solid-State Circuits, Vol. 24, No. 2, April 1989, pp.388-393
JHE	"High-Performance Embedded SOI DRAM Architecture for the Low-Power Supply", Yamauchi et al., IEEE Journal of Solid-State Circuits, Vol. 35, No. 8, August 2000, pp.1169-1178
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JHE	"A Capacitorless DRAM Cell on SOI Substrate", Wann et al., IEEE IEDM, 1993, pp.635-638

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JM	"High-Endurance Ultra-Thin Tunnel Oxide in MONOS Device Structure for Dynamic Memory Application", Wann et al., IEEE Electron Device Letters, Vol. 16, No. 11, November 1995, pp.491-493
JM	"Hot-Carrier Effects in Thin-Film Fully Depleted SOI MOSFET's", Ma et al., IEEE Electron Device Letters, Vol. 15, No. 6, June 1994, pp.218-220
JM	"Design Analysis of Thin-Body Silicide Source/Drain Devices", 2001 IEEE International SOI Conference, October 2001, pp.21-22
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JM	"High-Field Transport of Inversion-Layer Electrons and Holes Including Velocity Overshoot", Assaderaghi et al., IEEE Transactions on Electron Devices, Vol. 44, No. 4, April 1997, pp.664-671
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PTO-1449 (Modified)	ATTY. DOCKET NO. 211.001-D4-US	SERIAL NUMBER 10/727,742
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT		

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JM	EP 1 288 955 A2	3/2003	European			
JM	EP 1 280 205 A2	1/2003	European			
JM	EP 1 253 634 A2	10/2002	European			
JM	EP 1 241 708 A2	9/2002	European			
JM	EP 1 209 747 A2	5/2002	European			
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JM	EP 1 162 744 A1	12/2001	European			
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JM	EP 0 924 766 A2	6/1999	European			
JM	EP 0 920 059 A2	6/1999	European			
JM	EP 0 869 511 A2	10/1998	European			
JM	EP 0 860 878 A2	8/1998	European			
JM	EP 0 858 109 A2	8/1998	European			
JM	EP 0 844 671 B1	11/2002	European			
JM	EP 0 836 194 B1	5/2000	European			
JM	EP 0 788 165 A2	8/1997	European			
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JM	EP 0 725 402 B1	9/2002	European			
JM	EP 0 689 252 B1	8/2000	European			
JM	EP 0 682 370 B1	9/2000	European			
JM	EP 0 642 173 B1	7/1999	European			
JM	EP 0 642 173 A1	3/1995	European			
JM	EP 0 606 758 B1	9/2000	European			
JM	EP 0 601 590 B1	4/2000	European			
JM	EP 0 599 506 A1	6/1994	European			
JM	EP 0 599 388 B1	8/2000	European			
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JM	EP 0 359 551 B1	12/1994	European			
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JM	EP 0 350 057 B1	1/1990	European			
JM	EP 0 333 426 B1	7/1996	European			
JM	EP 0 300 157 B1	5/1993	European			
JM	EP 0 253 631 B1	4/1992	European			
JM	EP 0 245 515 B1	4/1997	European			
JM	EP 0 207 619 B1	8/1991	European			
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JMC	5,568,356	10/1996	Schwartz			
JMC	5,627,092	5/1997	Alsmeier et al.			
JMC	5,631,186	5/1997	Park et al.			
JMC	5,740,099	4/1998	Tanigawa			
JMC	5,877,978	3/1999	Morishita et al.			
JMC	5,930,648	7/1999	Yang			
JMC	5,939,745	8/1999	Park et al.			
JMC	5,943,258	8/1999	Houston et al.			
JMC	5,968,840	10/1999	Park et al.			
JMC	5,977,578	11/1999	Tang			
JMC	6,018,172	1/2000	Hidada et al.			

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JM	JP 8 274277	10/1996	Japanese			
JM	JP 9 82912	3/1997	Japanese			

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JR	2002/0064913	5/2002	Adkisson et al.			
JR	2002/0072155	6/2002	Liu et al.			
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JMC	6,617,651	9/2003	Ohsawa			
JMC	6,531,754	3/2003	Nagano et al.			
JMC	2002/0036322	3/2002	Divakauni et al.			

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JMC	2003-243528	8/2003	Japanese			X
JMC	2002-94027	3/2002	Japanese			X
JMC	2002-176154	6/2002	Japanese			X
JMC	2002-246571	8/2002	Japanese			X
JMC	2002-329795	11/2002	Japanese			X
JMC	2002-343886	11/2002	Japanese			X
JMC	2002-353080	12/2002	Japanese			X
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JM	2003-100900	4/2003	Japanese			X
JM	2003-132682	5/2003	Japanese			X
JM	2003-203967	7/2003	Japanese			X
JM	2003-243528	8/2003	Japanese			X
JM	09046688	2/1997	Japanese			X
JM	JP 8-213624	8/1996	Japanese			X
JM	JP 3-171768	7/1991	Japanese			X

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